Title (en)
METHOD, SYSTEM, AND ARTICLE OF MANUFACTURE FOR IMPLEMENTING METAL-FILL

Title (de)
VERFAHREN, SYSTEM UND HERSTELLUNGSARTIKELZUR IMPLEMENTIERUNG EINER METALLFÜLLUNG

Title (fr)
PROCEDE, SYSTEME ET ARTICLE DESTINES A LA MISE EN OEUVRE D'UNE TECHNIQUE DE REMPLISSAGE METALLIQUE

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Application
EP 03786859 A 20031119

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Abstract (en)
[origin: WO2004047001A2] Disclosed is a method, system, and article of manufacture for a one-pass approach for implementing metal-fill for an integrated circuit. Also disclosed is a method, system, and article of manufacture for implementing metal-fill that is coupled to a tie-off connection. An approach that is disclosed comprises a method, system, and article of manufacture for implementing metal-fill having an elongated shape that corresponds to the length of whitespace. Also disclosed is the aspect of implementing metal-fill that matches the routing direction. Yet another disclosure is an implementation of a place & route tool incorporating an integrated metal-fill mechanism.

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IPC 8 full level
G06F 17/50 (2006.01)

IPC 8 main group level
G06K (2006.01)

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